

# DP2307 P-Channel Enhancement Mode Field Effect Transistor

## **General description**

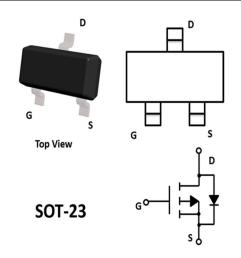
P-Channel Enhancement Mode Field Effect Transistor

#### Features:

- V<sub>DS</sub> : -30V
- I<sub>D</sub>: -3.0A
- $R_{DS(ON)}$ ( at  $V_{GS}=-10V$ ) < 85 mohm
- $R_{DS(ON)}$ ( at  $V_{GS}=-4.5V$ ) < 105 mohm
- Trench Power LV MOSFET technology
- High density cell design for Low R<sub>DS(ON)</sub>
- High Speed switching

#### **Applications**

- PMW applications
- Load switch
- Power management



#### **Device Marking Code:**

Device Type	Device Marking
DP2307	A7SHB

#### Absolute Maximum Ratings (TA=25°Cunless otherwise noted)

Pa	rameter	Symbol	Maximum	Unit	
Drain-source Voltage		V <sub>DS</sub>	-30	V	
Gate-source Voltage		$V_{GS}$	±2 <b>0</b>	V	
Drain Current	T <sub>A</sub> =25℃ @ Steady State		-3.0	А	
Drain Current	TA=70°C @ Steady State	I <sub>D</sub>	-2.4	Α	
Pulsed Drain Current <sup>A</sup>		Ірм	-13	A	
Total Power Dissipation @ T <sub>A</sub> =25 °C		P <sub>D</sub>	1.1	W	
Thermal Resistance Junction	n-to-Ambient <sup>B</sup>	$R_{ heta}$ JA	113	°C / W	
Junction and Storage Temperature Range		Тл ,Тѕтс	<b>-</b> 55∼+150	$^{\circ}$	

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## **DP2307**



#### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units	
Static Parameter							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =-250μA	-30			V	
Zero Gate Voltage Drain Current	Ioss	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V			-1	μA	
Gate-Body Leakage Current	Igss	$V_{GS}$ = $\pm 20$ V, $V_{DS}$ =0V			±100	nA	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.5	-2.4	٧	
Static Drain-Source On-Resistance	_	V <sub>GS</sub> = -10V, I <sub>D</sub> =-3.0A		60	85	mΩ	
	Rds(on)	V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-2.0A		80	105		
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3.0A,V <sub>GS</sub> =0V		-0.8	-1.2	V	
Maximum Body-Diode Continuous Current	Is				-3.0	А	
Dynamic Parameters							
Input Capacitance	C <sub>iss</sub>			375		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,f=1MHZ		63			
Reverse Transfer Capacitance	C <sub>rss</sub>			47			
Switching Parameters				I			
Total Gate Charge	$Q_g$			4.2			
Gate Source Charge	$Q_gs$	V <sub>GS</sub> =-10V,V <sub>DS</sub> =-15V,I <sub>D</sub> =-3.0		1.0		nC	
Gate Drain Charge	$Q_gd$			1.3			
Turn-on Delay Time	t <sub>D(on)</sub>	$V_{GS}$ =-10V, $V_{DD}$ =-15V, $R_{L}$ =15 $\Omega$ , $I_{D}$ =-1A, $R_{GEN}$ =2.5 $\Omega$		14		ns	
Turn-on Rise Time	t <sub>r</sub>			61			
Turn-off Delay Time	t <sub>D(off)</sub>			19			
Turn-off Fall Time	t <sub>f</sub>			10			

A.Pulse Test: Pulse Width  $\leq$  300us, Duty cycle  $\leq$  2%.

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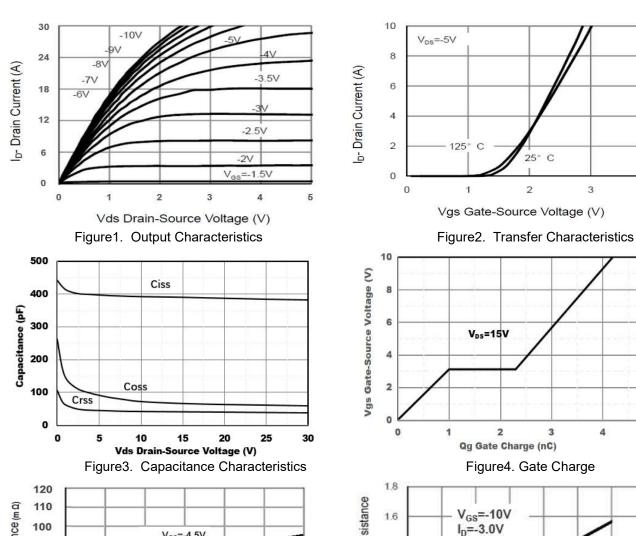
B.Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



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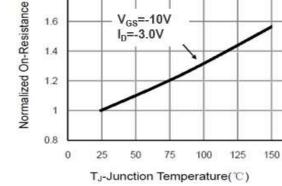
175

#### **Typical Performance Characteristics**



Rdson On-Resistance (m a) 100 V<sub>GS</sub>=-4.5V 90 80 V<sub>GS</sub>=-10V 70 60 50 40 2 5 0 3 6 I<sub>D</sub>- Drain Current (A)

Figure 5. Drain-Source on Resistance



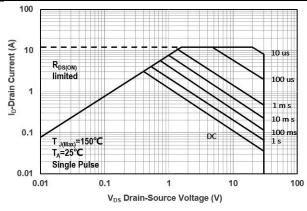
1.4

Figure6. Drain-Source on Resistance

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V<sub>OUT</sub>

V<sub>IN</sub>

SD%

PULSE WIDTH

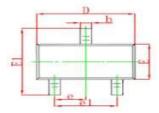
toff

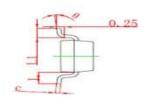
tof

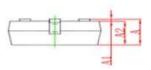
Figure7. Safe Operation Area

Figure8. Switching wave

## **SOT-23 Package Outline**

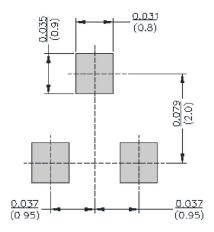






Symbol	Dimentions in Millimeter		Dimentions in Inches	
	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0 °	8 °	0 °	8 *

## **SOT-23 Suggested Pad Layout**



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